Peak gate voltage (T_j=25 ; duration 20μs FIG.7)	V_{GM}	1	kV

ELECTRICAL CHARACTERISTICS (T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	V_D =12V R_L =33Ω	- -	MAX.	50	mA
V_{GT}		- -	MAX.	1.3	V
V_{GD}	V_D =V_{DRM} T_j=125 R_L =3.3kΩ	- -	MIN.	0.2	V
I_L	I_G=1.2I_{GT}	-	MAX.	80	mA
				120	
I_H	I_T =1A		MAX.	70	mA
dV/dt	V_D=1070V Gate Open T_j=125		MIN.	1500	V/μs
(dI/dt)c	(dV/dt)c=20V/μs T_j=125		MIN.	28	A/ms
t_{gd}	I_G=80mA I_A=400mA I_R=40mA T_j=25		TYP.	12	μs
t_{gt}				80	

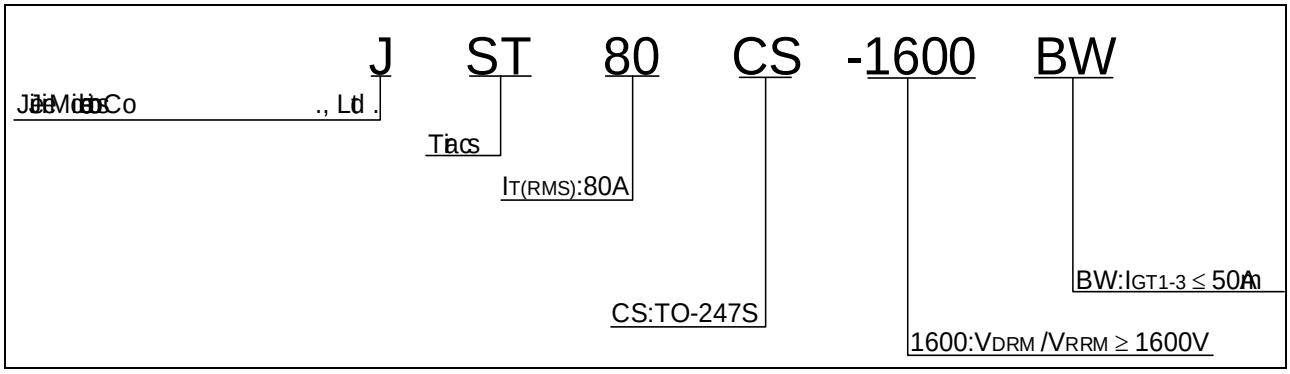
STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	I_{TM} =120A t_p=380μs	T_j=25	1.9	V
V_{TO}	Threshold voltage	T_j=125	0.71	V
R_D	Dynamic resistance	T_j=125	23	mΩ
I_{DRM}	V_D=V_{DRM} V_R =V_{RRM}	T_j=25	20	μA
I_{RRM}		T_j=125	12	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$			

ORDERING INFORMATION



MARKING

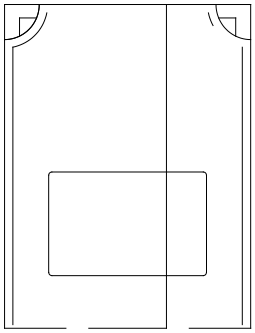
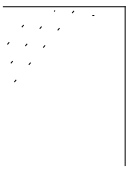


FIG.1: Maximum RMS on-state current vs. case temperature

FIG.2: RMS on-state current vs. ambient temperature

FIG.7

PACKAGE MECHANICAL DATA



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